What we claim is,

1.	An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

(11-20) and (1-100) sides; and

5	a longer slanting edge (L) and a shorter slanting edge (S) formed at two obversely-clockwise neighboring corners on a side opposite to the (11-20) side as a reference side.

2.	The obverse/reverse discriminative rectangular nitride semiconductor wafer according to claim 1, wherein lengths of the longer slanting edge (L) and the shorter slanting edge (S)

10	satisfy inequalities $S < L$, $K/40 \leq L \leq K/12$ and $K/40 \leq S \leq K/16$, where K is a sum of lengths of four sides of the rectangular wafer.

3.	An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

(11-20) and (1-100) sides; and

15	a longer slanting edge (L) and a shorter slanting edge (S) formed at two obversely-clockwise neighboring corners on a side opposite to the (1-100) side as a reference side.

4.	The obverse/reverse discriminative rectangular nitride semiconductor wafer according to claim 3, wherein lengths of the longer slanting edge (L) and the shorter slanting edge (S)

20	satisfy inequalities $S < L$, $K/40 \leq L \leq K/12$ and $K/40 \leq S \leq K/16$, where K is a sum of lengths of four sides of the rectangular wafer.

5.	An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

(11-20) and (1-100) sides; and

25	an asymmetric slanting edge formed at an obverse-counterclockwise corner of a

(-1-120) side opposite to the (11-20) side as a reference side,

the asymmetric slanting edge inclining to an obverse-counterclockwise neighboring side at an angle Θ between 5degrees and 40degrees ($5° \leqq \Theta \leqq 40°$) and having a length between K/40 and K/16, where K is a sum of lengths of four sides of the rectangular wafer.

5   6.   An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

(11-20) and (1-100) sides; and

an asymmetric slanting edge formed at an obverse-counterclockwise corner of a (-1100) side opposite to the (1-100) side as a reference side,

10   the asymmetric slanting edge inclining to an obverse-counterclockwise neighboring side at an angle Θ between 5degrees and 40degrees ($5° \leqq \Theta \leqq 40°$) and having a length between K/40 and K/16, where K is a sum of lengths of four sides of the rectangular wafer.

7.   An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1); and

15   (11-20) and (1-100) sides,

wherein the sides are bevelled asymmetrically for an obverse and a reverse and an obverse bevelling width (g) is smaller than a reverse bevelling width (h).

8.   The obverse/reverse discriminative rectangular nitride semiconductor wafer according to claim 7, wherein the obverse bevelling width (g) and the reverse bevelling with (h) satisfy

20   inequalities of g < h, $100 \mu m \leqq g \leqq 400 \mu m$ and $300 \mu m \leqq h \leqq 1000 \mu m$.

9.   An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

(11-20) and (1-100) sides; and

characters written in normal posture on the obverse surface in parallel with the (11-20)

25   side along a [1-100] direction by laser marking.

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10. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

(11-20) and (1-100) sides; and

characters written in inverse posture on the obverse surface in parallel with the (11-20)

5   side along a [1-100] direction by laser marking.

11. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

a reverse surface opposite to the obverse surface;

(11-20) and (1-100) sides; and

10   characters written in normal posture on the reverse surface in parallel with the (11-20)

side in a [1-100] direction by laser marking.

12. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

a reverse surface opposite to the obverse surface;

15   (11-20) and (1-100) sides; and

characters written in inverse posture on the reverse surface in parallel with the (11-20)

side in a [1-100] direction by laser marking.

13. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

20   (11-20) and (1-100) sides; and

characters written in normal posture on the obverse surface in parallel with the (1-100)

side in a [11-20] direction by laser marking.

14. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

25   (11-20) and (1-100) sides; and

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characters written in inverse posture on the obverse surface in parallel with (1-100) side in a [11-20] direction by laser marking.

15. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

a reverse surface opposite to the obverse surface;

(11-20) and (1-100) sides; and

characters written in normal posture on the reverse surface in a [11-20] direction in parallel with the (1-100) side by laser marking.

16. An obverse/reverse discriminative rectangular nitride semiconductor wafer having:

an obverse surface of (0001) or (000-1);

a reverse surface opposite to the obverse surface;

(11-20) and (1-100) sides; and

characters written in inverse posture on the reverse surface in a [11-20] direction in parallel with the (1-100) side by laser marking.